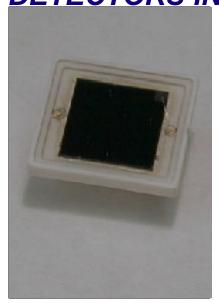
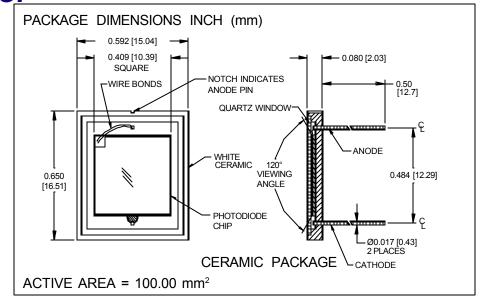
PHOTONIC DETECTORS INC.

Silicon Photodiode, U.V. Enhanced Photovoltaic Type PDU-V110-Q





FEATURES

Low noise

- U.V. enhanced
- High shunt resistance
- Quartz window

DESCRIPTION

The **PDU-V110-Q** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for low noise photovoltaic applications. Packaged in low profile ceramic substrate with a quartz window.

APPLICATIONS

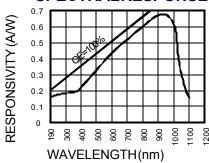
- Spectometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		75	V
T _{STG}	Storage Temperature	-20	+80	∘C
To	Operating Temperature Range	-20	+60	⊙C
Ts	Soldering Temperature*		+220	∘C
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	0.9	1.2		m A
ΙD	Dark Current	$H = 0, V_R = 10 \text{ mV}$		200	333	pA
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	30	50		МΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃
Сл	Junction Capacitance	H = 0, V _R = 0 V**		10,000	12,000	рF
λrange	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	V_R = 0 V, λ = 254 nm	.12	.18		A/W
VBR	Breakdown Voltage	I = 10 μA	5	10		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		2.0x10 ⁻¹⁴		W/ √ Hz
tr	Response Time	RL = 1 KΩ V _R = 0 V		2000		nS